

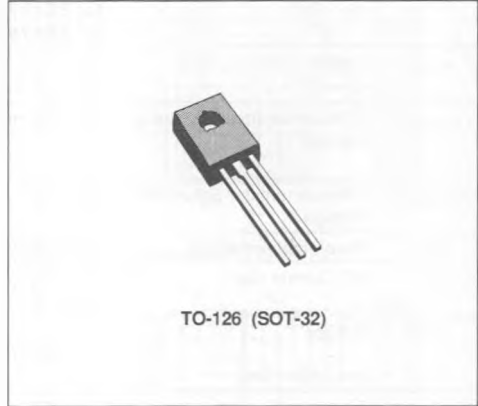


MEDIUM POWER LINEAR AND SWITCHING APPLICATIONS

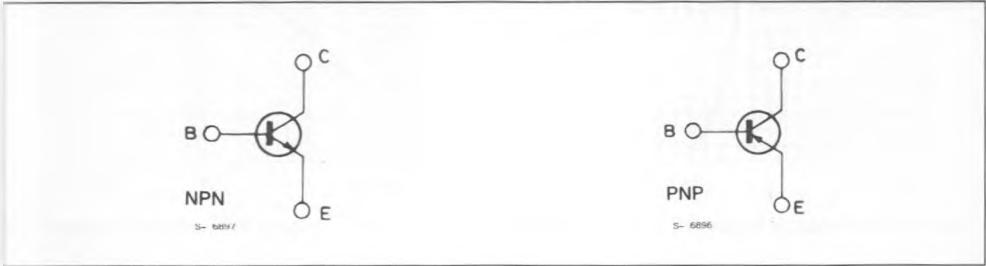
DESCRIPTION

The BD175, BD177 and BD179 are silicon epitaxial-base NPN power transistors in Jedec TO-126 plastic package intended for use in medium power linear and switching applications.

The complementary PNP types are the BD176, BD178 and BD180.



INTERNAL SCHEMATIC DIAGRAMS



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	NPN PNP*	Value			Unit
			BD175 BD176	BD177 BD178	BD179 BD180	
V_{CBO}	Collector-base Voltage ($I_E = 0$)		45	60	80	V
V_{CEO}	Collector-emitter Voltage ($I_B = 0$)		45	60	80	V
V_{EBO}	Emitter-base Voltage ($I_C = 0$)		5			V
I_C	Collector Current		3			A
I_{CM}	Collector Peak Current		7			A
P_{tot}	Total Power Dissipation at $T_{case} \leq 25^\circ C$		30			W
T_{stg}	Storage Temperature		- 65 to 150			$^\circ C$
T_j	Junction Temperature		150			$^\circ C$

* For PNP types voltage and current values are negative.

THERMAL DATA

$R_{th\ j-case}$	Thermal Resistance Junction-case	Max	4.16	°C/W
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ELECTRICAL CHARACTERISTICS ($T_{case} = 25\text{ °C}$ unless otherwise specified)

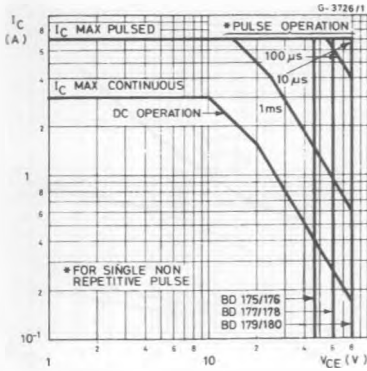
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cutoff Current ($I_E = 0$)	for BD175/76 $V_{CB} = 45\text{ V}$ for BD177/78 $V_{CB} = 60\text{ V}$ for BD179/80 $V_{CB} = 80\text{ V}$			100 100 100	μA μA μA
I_{EBO}	Emitter Cutoff Current ($I_C = 0$)	$V_{EB} = 5\text{ V}$			1	mA
$V_{CE(sus)}^*$	Collector-emitter Sustaining Voltage	$I_C = 100\text{ mA}$ for BD175/76 for BD177/78 for BD179/80	45 60 80			V V V
$V_{CE(sat)}^*$	Collector-emitter Saturation Voltage	$I_C = 1\text{ A}$ $I_B = 0.1\text{ A}$			0.8	V
V_{BE}^*	Base-emitter Voltage	$I_C = 1\text{ A}$ $V_{CE} = 2\text{ V}$			1.3	V
h_{FE}^*	DC Current Gain	$I_C = 150\text{ mA}$ $V_{CE} = 2\text{ V}$ $I_C = 1\text{ A}$ $V_{CE} = 2\text{ V}$	40 15			
h_{FE}	Groups** 6 10 (only BD175/6) 16	$I_C = 150\text{ mA}$ $V_{CE} = 2\text{ V}$	40 63 100		100 160 250	
f_T	Transition Frequency	$I_C = 250\text{ mA}$ $V_{CE} = 10\text{ V}$	3			MHz

* Pulsed : pulse duration = 300 μs , duty cycle $\leq 1.5\%$.

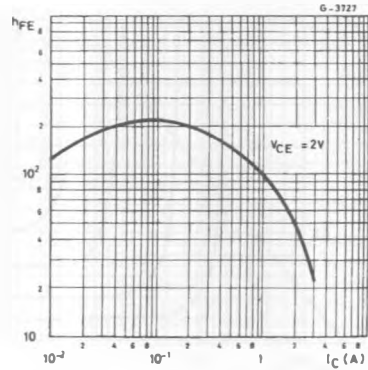
** Only on request.

For PNP types voltage and current values are negative.

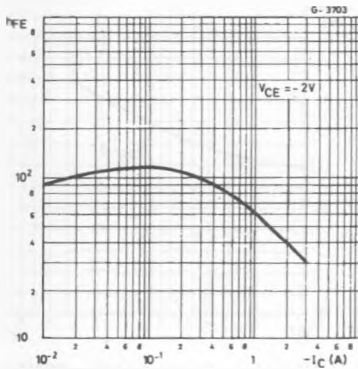
Operating Areas.



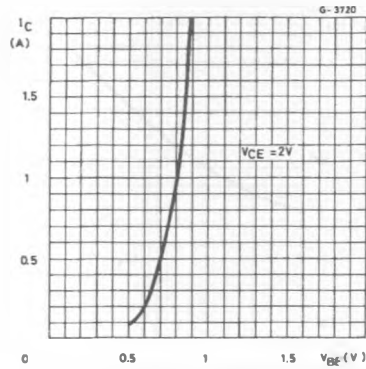
DC Current Gain (NPN types).



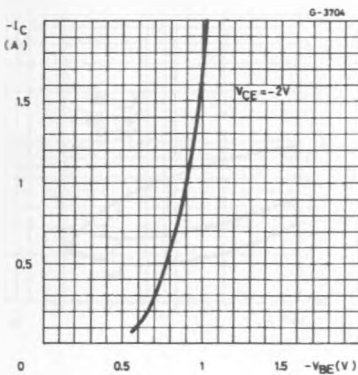
DC Current Gain (PNP types)



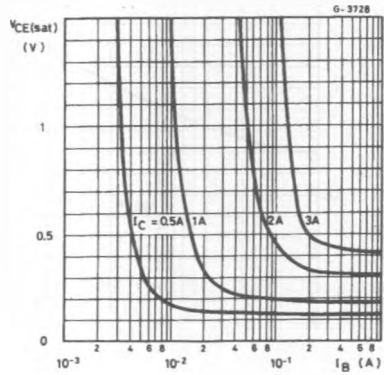
DC Transconductance (NPN types).



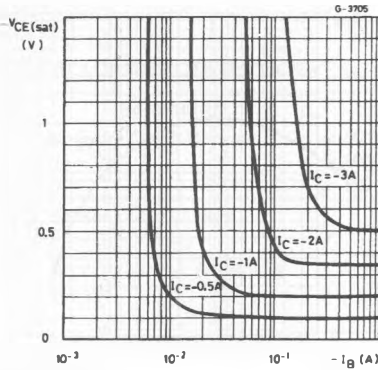
DC Transconductance (PNP types)



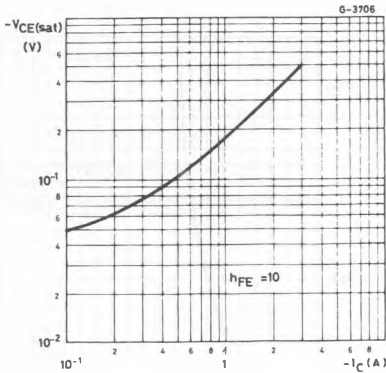
Collector-emitter Saturation Voltage (NPN types).



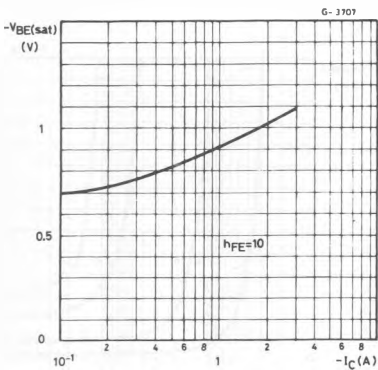
Collector-emitter Saturation Voltage (PNP types).



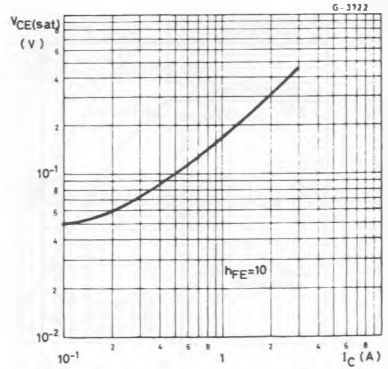
Collector-emitter Saturation Voltage (PNP types).



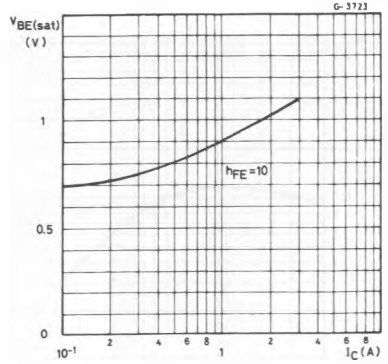
Base-emitter Saturation Voltage (PNP types).



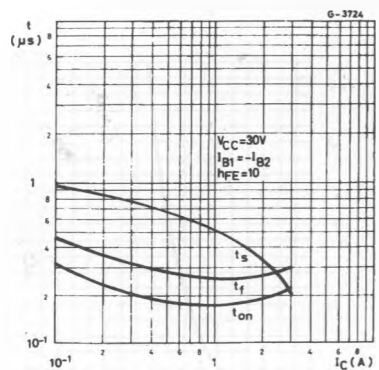
Collector-emitter Saturation Voltage (NPN types).



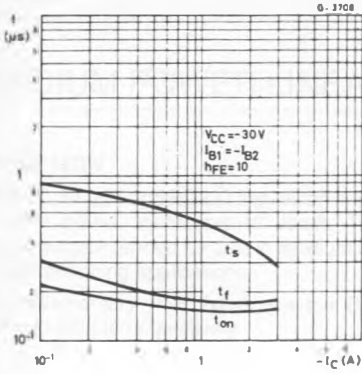
Base-emitter Saturation Voltage (NPN types).



Saturated Switching Characteristics (NPN types).



Saturated Switching Characteristics (PNP types).



Power Derating Chart.

